

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

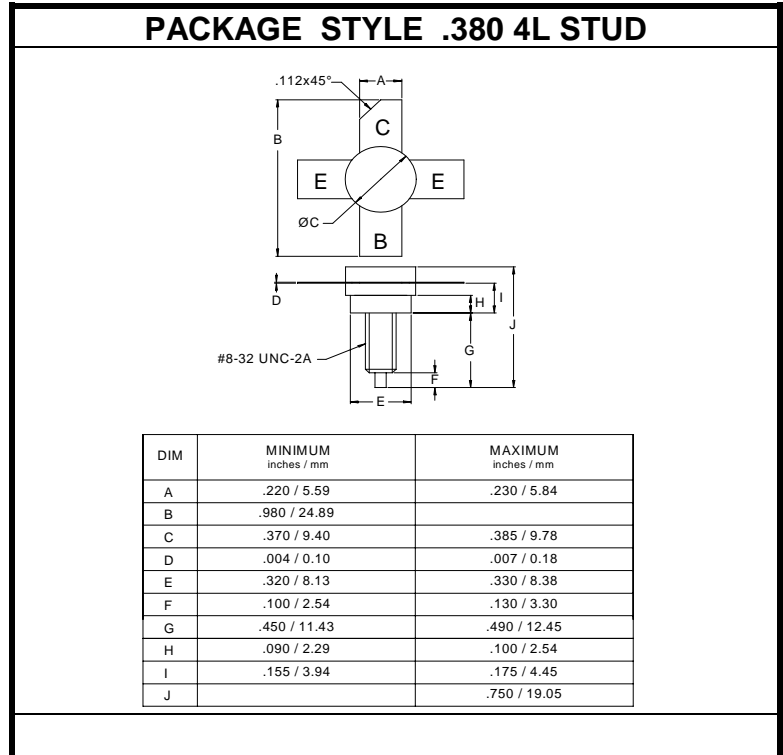
The **ASI BLY92A** is an NPN power transistor designed for 138-175 MHz VHF communications. It utilizes emitter ballasting to provide high VSWR handling capability.

**FEATURES:**

- Common Emitter, 28 V operation
- $P_G = 10$  dB at 10W/175 MHz
- **Omnigold™** Metalization System
- High VSWR capability

**MAXIMUM RATINGS**

$I_C$	1.0 A
$V_{CBO}$	65 V
$V_{CEO}$	35 V
$V_{EBO}$	4.0 V
$P_{DISS}$	13.0 W
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	13.5 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 200$ mA	65			V
$BV_{CES}$	$I_C = 200$ mA	65			V
$BV_{CEO}$	$I_C = 200$ mA	35			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			1.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 200$ mA	5.0		200	---
$C_{ob}$	$V_{CB} = 30$ V $f = 1.0$ MHz			15	pF
$P_G$ $\eta_c$	$V_{CC} = 28$ V $P_{OUT} = 10$ W $f = 175$ MHz $P_{IN} = 1.0$ W	10	60		dB %

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.